8-Bit Serial or Parallel-Input/ **Serial-Output Shift Register High-Performance Silicon-Gate CMOS**

The MC74HC165A is identical in pinout to the LS165. The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

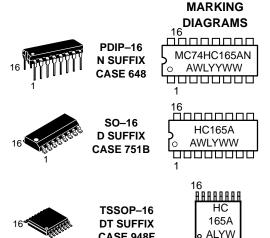
This device is an 8-bit shift register with complementary outputs from the last stage. Data may be loaded into the register either in parallel or in serial form. When the Serial Shift/Parallel Load input is low, the data is loaded asynchronously in parallel. When the Serial Shift/Parallel Load input is high, the data is loaded serially on the rising edge of either Clock or Clock Inhibit (see the Function Table).

The 2-input NOR clock may be used either by combining two independent clock sources or by designating one of the clock inputs to act as a clock inhibit.

- Output Drive Capability: 10 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2 to 6 V
- Low Input Current: 1 μA
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with the Requirements Defined by JEDEC Standard No. 7A
- Chip Complexity: 286 FETs or 71.5 Equivalent Gates



http://onsemi.com



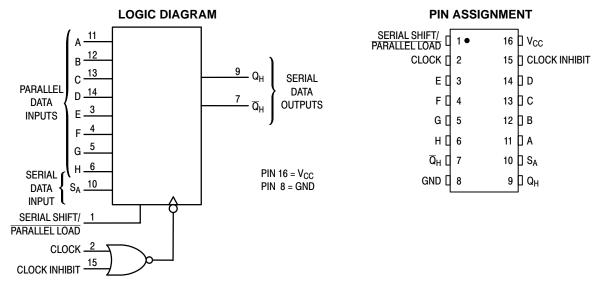
= Assembly Location WL or L = Wafer Lot

CASE 948F

YY or Y = YearWW or W = Work Week

ORDERING INFORMATION

| Device | Package | Shipping |
|----------------|----------|-------------|
| MC74HC165AN | PDIP-16 | 2000 / Box |
| MC74HC165AD | SOIC-16 | 48 / Rail |
| MC74HC165ADR2 | SOIC-16 | 2500 / Reel |
| MC74HC165ADT | TSSOP-16 | 96 / Rail |
| MC74HC165ADTR2 | TSSOP-16 | 2500 / Reel |



FUNCTION TABLE

| Inputs | | | Interna | Internal Stages Out | | | | |
|--------------------------------|--------------|------------------|----------------|---------------------|----------------|------------------------------------|------------------------------------|--------------------------------|
| Serial Shift/ Parallel Load | Clock | Clock Inhibit | S _A | A – H | Q _A | Q _B | Q _H | Operation |
| L | Х | Х | Х | a h | а | b | h | Asynchronous Parallel Load |
| H H | \(\sigma \) | L L | L H | X | L H | Q _{An} Q _{An} | Q _{Gn} Q _{Gn} | Serial Shift via Clock |
| H H | L L | <i></i> | L H | X | L H | Q _{An} Q _{An} | Q _{Gn} Q _{Gn} | Serial Shift via Clock Inhibit |
| H H | X H | H X | X X | X X | No Change | | | Inhibited Clock |
| Н | L | L | Х | Х | | No Change | | No Clock |

X = don't care $Q_{An} - Q_{Gn} = Data shifted from the preceding stage$

MAXIMUM RATINGS*

| Symbol | Parameter | Value | Unit |
|------------------|---|--------------------------|------|
| V _{CC} | DC Supply Voltage (Referenced to GND) | - 0.5 to + 7.0 | V |
| V _{in} | DC Input Voltage (Referenced to GND) | -0.5 to $V_{CC} + 0.5$ | V |
| V _{out} | DC Output Voltage (Referenced to GND) | -0.5 to $V_{CC} + 0.5$ | V |
| I _{in} | DC Input Current, per Pin | ± 20 | mA |
| l _{out} | DC Output Current, per Pin | ± 25 | mA |
| Icc | DC Supply Current, V _{CC} and GND Pins | ± 50 | mA |
| P _D | Power Dissipation in Still Air Plastic DIP† SOIC Package† TSSOP Package† | 750 500 450 | mW |
| T _{stg} | Storage Temperature | - 65 to + 150 | °C |
| TL | Lead Temperature, 1 mm from Case for 10 Seconds (Plastic DIP, SOIC or TSSOP Package) | 260 | °C |

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND \leq (V_{in} or V_{out}) \leq V_{CC} .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

SOIC Package: $-~7~mW/^{\circ}C$ from 65° to $125^{\circ}C$

TSSOP Package: - 6.1 mW/°C from 65° to 125°C

For high frequency or heavy load considerations, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

RECOMMENDED OPERATING CONDITIONS

| Symbol | Parameter | Min | Max | Unit | |
|------------------------------------|--|---|-------------|---------------------------|----|
| V _{CC} | DC Supply Voltage (Referenced to GND) | | | 6.0 | V |
| V _{in} , V _{out} | DC Input Voltage, Output Voltage (Referenced to GND) | | | V _{CC} | V |
| T _A | Operating Temperature, All Package Types | | | + 125 | °C |
| t _r , t _f | Input Rise and Fall Time (Figure 1) | $V_{CC} = 2.0 \text{ V}$ $V_{CC} = 3.0 \text{ V}$ $V_{CC} = 4.5 \text{ V}$ $V_{CC} = 6.0 \text{ V}$ | 0 0 0 | 1000 600 500 400 | ns |

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

| | | | | Guaranteed Limit | | | |
|-----------------|--------------------------------------|---|--------------------------|----------------------------|----------------------------|----------------------------|------|
| Symbol | Parameter | Test Conditions | V _{CC} V | – 55 to 25°C | ≤ 85°C | ≤ 125°C | Unit |
| V _{IH} | Minimum High–Level Input Voltage | $V_{out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$ $ I_{out} \le 20 \mu\text{A}$ | 2.0 3.0 4.5 6.0 | 1.5 2.1 3.15 4.2 | 1.5 2.1 3.15 4.2 | 1.5 2.1 3.15 4.2 | V |
| V _{IL} | Maximum Low–Level Input Voltage | $V_{out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$ $ I_{out} \le 20 \mu\text{A}$ | 2.0 3.0 4.5 6.0 | 0.5 0.9 1.35 1.80 | 0.5 0.9 1.35 1.80 | 0.5 0.9 1.35 1.80 | V |
| V _{OH} | Minimum High-Level Output Voltage | $V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \le 20 \mu\text{A}$ | 2.0 4.5 6.0 | 1.9 4.4 5.9 | 1.9 4.4 5.9 | 1.9 4.4 5.9 | V |
| | | $\begin{split} V_{\text{in}} = V_{\text{IH}} \text{ or } V_{\text{IL}} & I_{\text{out}} \leq 2.4 \text{ mA} \\ I_{\text{out}} \leq 4.0 \text{ mA} \\ I_{\text{out}} \leq 5.2 \text{ mA} \end{split}$ | 3.0 4.5 6.0 | 2.48 3.98 5.48 | 2.34 3.84 5.34 | 2.20 3.70 5.20 | V |

^{*}Maximum Ratings are those values beyond which damage to the device may occur.

Functional operation should be restricted to the Recommended Operating Conditions.

[†]Derating — Plastic DIP: – 10 mW/°C from 65° to 125°C

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

| | | | | Guaranteed Limit | | | |
|-----------------|---|---|----------------------|----------------------|----------------------|----------------------|------|
| Symbol | Parameter | Test Conditions | v _{cc} v | – 55 to 25°C | ≤ 85°C | ≤ 125°C | Unit |
| V _{OL} | Maximum Low–Level Output Voltage | $V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \le 20 \ \mu\text{A}$ | 2.0 4.5 6.0 | 0.1 0.1 0.1 | 0.1 0.1 0.1 | 0.1 0.1 0.1 | V |
| | | $V_{in} = V_{IH} \text{ or } V_{IL} \qquad I_{out} \le 2.4 \text{ mA} $ $ I_{out} \le 4.0 \text{ mA} $ $ I_{out} \le 5.2 \text{ mA} $ | 3.0 4.5 6.0 | 0.26 0.26 0.26 | 0.33 0.33 0.33 | 0.40 0.40 0.40 | |
| I _{in} | Maximum Input Leakage Current | V _{in} = V _{CC} or GND | 6.0 | ± 0.1 | ± 1.0 | ± 1.0 | μА |
| I _{CC} | Maximum Quiescent Supply Current (per Package) | $V_{in} = V_{CC}$ or GND $I_{out} = 0 \mu A$ | 6.0 | 4 | 40 | 160 | μΑ |

NOTE: Information on typical parametric values can be found in Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

AC ELECTRICAL CHARACTERISTICS (C_L = 50 pF, Input t_r = t_f = 6 ns)

| | | | Guaranteed Limit | | | |
|--|--|--------------------------|-----------------------|-----------------------|-----------------------|------|
| Symbol | Parameter | V _{CC} V | – 55 to 25°C | ≤ 85°C | ≤ 125°C | Unit |
| f _{max} | Maximum Clock Frequency (50% Duty Cycle) (Figures 1 and 8) | 2.0 3.0 4.5 6.0 | 6 18 30 35 | 4.8 17 24 28 | 4 15 20 24 | MHz |
| t _{PLH} , t _{PHL} | Maximum Propagation Delay, Clock (or Clock Inhibit) to Q_H or \overline{Q}_H (Figures 1 and 8) | 2.0 3.0 4.5 6.0 | 150 52 30 26 | 190 63 38 33 | 225 65 45 38 | ns |
| t _{PLH} , t _{PHL} | Maximum Propagation Delay, Serial Shift/Parallel Load to Q_H or \overline{Q}_H (Figures 2 and 8) | 2.0 3.0 4.5 6.0 | 175 58 35 30 | 220 70 44 37 | 265 72 53 45 | ns |
| t _{PLH} , t _{PHL} | Maximum Propagation Delay, Input H to Q _H or Q _H (Figures 3 and 8) | 2.0 3.0 4.5 6.0 | 150 52 30 26 | 190 63 38 33 | 225 65 45 38 | ns |
| t _{TLH} , t _{THL} | Maximum Output Transition Time, Any Output (Figures 1 and 8) | 2.0 3.0 4.5 6.0 | 75 27 15 13 | 95 32 19 16 | 110 36 22 19 | ns |
| C _{in} | Maximum Input Capacitance | _ | 10 | 10 | 10 | pF |

NOTES:

- 1. For propagation delays with loads other than 50 pF, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).
- 2. Information on typical parametric values can be found in Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

| | | Typical @ 25°C, V _{CC} = 5.0 V | |
|--------|--|---|----|
| C_PD | Power Dissipation Capacitance (Per Package)* | 40 | pF |

^{*} Used to determine the no–load dynamic power consumption: P_D = C_{PD} V_{CC}²f + I_{CC} V_{CC}. For load considerations, see Chapter 2 of the ON Semiconductor High–Speed CMOS Data Book (DL129/D).

TIMING REQUIREMENTS (Input $t_r = t_f = 6 \text{ ns}$)

| | | | Guaranteed Limit | | mit | |
|---------------------------------|---|--------------------------|---------------------------|---------------------------|---------------------------|------|
| Symbol | Parameter | V _{CC} | – 55 to 25°C | ≤ 85°C | ≤ 125°C | Unit |
| t _{su} | Minimum Setup Time, Parallel Data Inputs to Serial Shift/Parallel Load (Figure 4) | 2.0 3.0 4.5 6.0 | 75 30 15 13 | 95 40 19 16 | 110 55 22 19 | ns |
| t _{su} | Minimum Setup Time, Input SA to Clock (or Clock Inhibit) (Figure 5) | 2.0 3.0 4.5 6.0 | 75 30 15 13 | 95 40 19 16 | 110 55 22 19 | ns |
| t _{su} | Minimum Setup Time, Serial Shift/Parallel Load to Clock (or Clock Inhibit) (Figure 6) | 2.0 3.0 4.5 6.0 | 75 30 15 13 | 95 40 19 16 | 110 55 22 19 | ns |
| t _{su} | Minimum Setup Time, Clock to Clock Inhibit (Figure 7) | 2.0 3.0 4.5 6.0 | 75 30 15 13 | 95 40 19 16 | 110 55 22 19 | ns |
| t _h | Minimum Hold Time, Serial Shift/Parallel Load to Parallel Data Inputs (Figure 4) | 2.0 3.0 4.5 6.0 | 5 5 5 5 | 5 5 5 5 | 5 5 5 5 | ns |
| t _h | Minimum Hold Time, Clock (or Clock Inhibit) to Input SA (Figure 5) | 2.0 3.0 4.5 6.0 | 5 5 5 5 | 5 5 5 5 | 5 5 5 5 | ns |
| t _h | Minimum Hold Time, Clock (or Clock Inhibit) to Serial Shift/Parallel Load (Figure 6) | 2.0 3.0 4.5 6.0 | 5 5 5 5 | 5 5 5 5 | 5 5 5 5 | ns |
| t _{rec} | Minimum Recovery Time, Clock to Clock Inhibit (Figure 7) | 2.0 3.0 4.5 6.0 | 75 30 15 13 | 95 40 19 16 | 110 55 22 19 | ns |
| t _w | Minimum Pulse Width, Clock (or Clock Inhibit) (Figure 1) | 2.0 3.0 4.5 6.0 | 70 27 15 13 | 90 32 19 16 | 100 36 22 19 | ns |
| t _w | Minimum Pulse width, Serial Shift/Parallel Load (Figure 2) | 2.0 3.0 4.5 6.0 | 70 27 15 13 | 90 32 19 16 | 100 36 22 19 | ns |
| t _r , t _f | Maximum Input Rise and Fall Times (Figure 1) | 2.0 3.0 4.5 6.0 | 1000 800 500 400 | 1000 800 500 400 | 1000 800 500 400 | ns |

NOTE: Information on typical parametric values can be found in Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

PIN DESCRIPTIONS

INPUTS

A, B, C, D, E, F, G, H (Pins 11, 12, 13, 14, 3, 4, 5, 6)

Parallel Data inputs. Data on these inputs are asynchronously entered in parallel into the internal flip—flops when the Serial Shift/Parallel Load input is low.

SA (Pin 10)

Serial Data input. When the Serial Shift/Parallel Load input is high, data on this pin is serially entered into the first stage of the shift register with the rising edge of the Clock.

CONTROL INPUTS

Serial Shift/Parallel Load (Pin 1)

Data-entry control input. When a high level is applied to this pin, data at the Serial Data input (SA) are shifted into the register with the rising edge of the Clock. When a low level is applied to this pin, data at the Parallel Data inputs are asynchronously loaded into each of the eight internal stages.

Clock, Clock Inhibit (Pins 2, 15)

Clock inputs. These two clock inputs function identically. Either may be used as an active—high clock inhibit. However, to avoid double clocking, the inhibit input should go high only while the clock input is high.

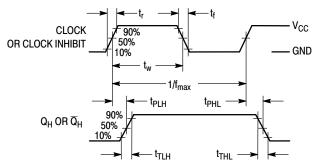
The shift register is completely static, allowing Clock rates down to DC in a continuous or intermittent mode.

OUTPUTS

Q_H, Q_H (Pins 9, 7)

Complementary Shift Register outputs. These pins are the noninverted and inverted outputs of the eighth stage of the shift register.

SWITCHING WAVEFORMS





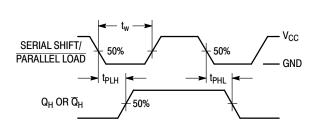


Figure 2. Parallel-Load Mode

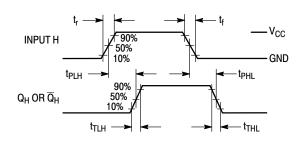


Figure 3. Parallel-Load Mode

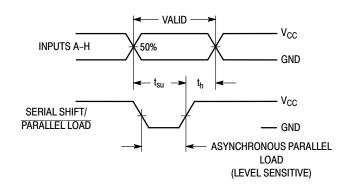


Figure 4. Parallel-Load Mode

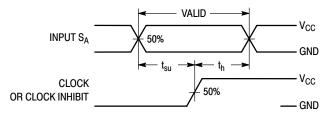


Figure 5. Serial-Shift Mode

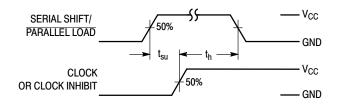


Figure 6. Serial-Shift Mode

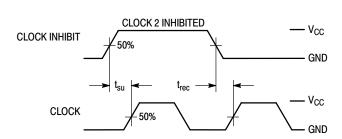
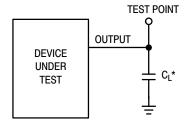


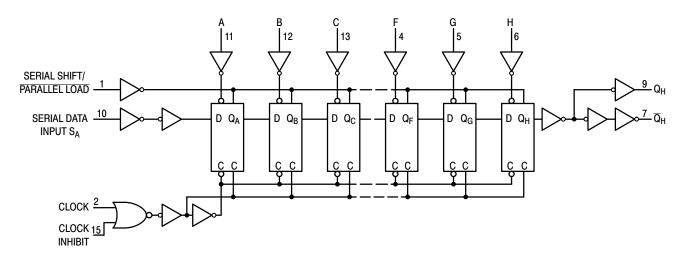
Figure 7. Serial-Shift, Clock-Inhibit Mode



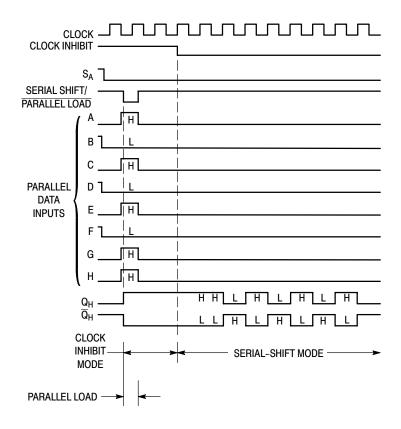
*Includes all probe and jig capacitance

Figure 8. Test Circuit

EXPANDED LOGIC DIAGRAM

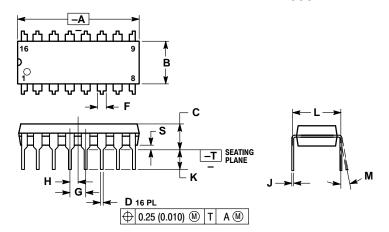


TIMING DIAGRAM



PACKAGE DIMENSIONS

PDIP-16 **N SUFFIX** CASE 648-08 ISSUE R



NOTES:

- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: INCH.

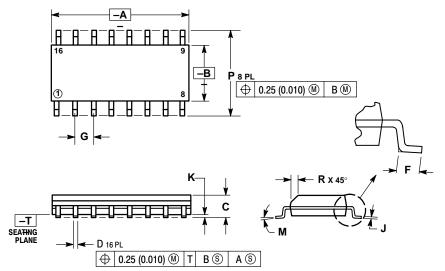
 3. DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.

 4. DIMENSION B DOES NOT INCLUDE MOLD FLASH.

 5. ROUNDED CORNERS OPTIONAL.

| | INC | HES | MILLIN | IETERS | | | | | |
|-----|-------|---------|--------|---------|--|--|--|--|--|
| DIM | MIN | MAX | MIN | MAX | | | | | |
| Α | 0.740 | 0.770 | 18.80 | 19.55 | | | | | |
| В | 0.250 | 0.270 | 6.35 | 6.85 | | | | | |
| С | 0.145 | 0.175 | 3.69 | 4.44 | | | | | |
| D | 0.015 | 0.021 | 0.39 | 0.53 | | | | | |
| F | 0.040 | 0.070 | 1.02 | 1.77 | | | | | |
| G | 0. | 100 BSC | 2 | .54 BSC | | | | | |
| Н | 0. | 050 BSC | 1 | .27 BSC | | | | | |
| J | 0.008 | 0.015 | 0.21 | 0.38 | | | | | |
| K | 0.110 | 0.130 | 2.80 | 3.30 | | | | | |
| L | 0.295 | 0.305 | 7.50 | 7.74 | | | | | |
| M | 0° | 10° | 0° | 10° | | | | | |
| S | 0.020 | 0.040 | 0.51 | 1 01 | | | | | |





NOTES:

- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: MILLIMETER.

 3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.

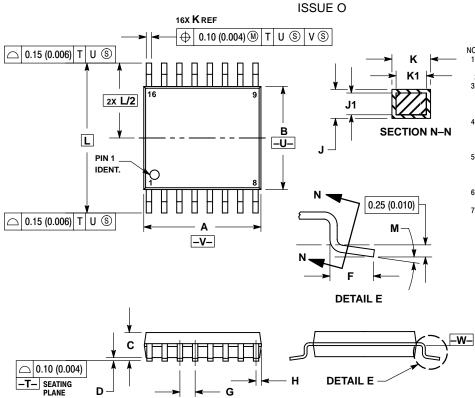
 4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.

 5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

| | MILLIM | ETERS | INC | HES |
|-----|--------|-------|-------|-------|
| DIM | MIN | MAX | MIN | MAX |
| Α | 9.80 | 10.00 | 0.386 | 0.393 |
| В | 3.80 | 4.00 | 0.150 | 0.157 |
| С | 1.35 | 1.75 | 0.054 | 0.068 |
| D | 0.35 | 0.49 | 0.014 | 0.019 |
| F | 0.40 | 1.25 | 0.016 | 0.049 |
| G | 1.2 | 7 BSC | 0.050 | BSC |
| J | 0.19 | 0.25 | 0.008 | 0.009 |
| K | 0.10 | 0.25 | 0.004 | 0.009 |
| M | 0° | 7° | 0° | 7° |
| P | 5.80 | 6.20 | 0.229 | 0.244 |
| R | 0.25 | 0.50 | 0.010 | 0.019 |

PACKAGE DIMENSIONS

TSSOP-16 **DT SUFFIX** CASE 948F-01



NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI
- Y14.5M, 1982. CONTROLLING DIMENSION: MILLIMETER.
- DIMENSION A DOES NOT INCLUDE MOLD FLASH.
 PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
- SIDE.

 DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.

 DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION. SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
- TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
- DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

| | MILLIN | IETERS | INC | HES | |
|-----|--------|--------|-----------|-------|--|
| DIM | MIN | MAX | MIN | MAX | |
| Α | 4.90 | 5.10 | 0.193 | 0.200 | |
| В | 4.30 | 4.50 | 0.169 | 0.177 | |
| C | | 1.20 | | 0.047 | |
| D | 0.05 | 0.15 | 0.002 | 0.006 | |
| F | 0.50 | 0.75 | 0.020 | 0.030 | |
| G | 0.65 | BSC | 0.026 | BSC | |
| Н | 0.18 | 0.28 | 0.007 | 0.011 | |
| 7 | 0.09 | 0.20 | 0.004 | 0.008 | |
| J1 | 0.09 | 0.16 | 0.004 | 0.006 | |
| K | 0.19 | 0.30 | 0.007 | 0.012 | |
| K1 | 0.19 | 0.25 | 0.007 | 0.010 | |
| L | 6.40 | | 0.252 BSC | | |
| M | 0 ° | 80 | 0 ° | gο | |

Notes

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer.

PUBLICATION ORDERING INFORMATION

NORTH AMERICA Literature Fulfillment:

Literature Distribution Center for ON Semiconductor P.O. Box 5163, Denver, Colorado 80217 USA

Phone: 303–675–2175 or 800–344–3860 Toll Free USA/Canada **Fax**: 303–675–2176 or 800–344–3867 Toll Free USA/Canada

Email: ONlit@hibbertco.com

Fax Response Line: 303-675-2167 or 800-344-3810 Toll Free USA/Canada

N. American Technical Support: 800-282-9855 Toll Free USA/Canada

EUROPE: LDC for ON Semiconductor - European Support

German Phone: (+1) 303-308-7140 (M-F 1:00pm to 5:00pm Munich Time)

Email: ONlit-german@hibbertco.com

French Phone: (+1) 303–308–7141 (M–F 1:00pm to 5:00pm Toulouse Time)

Email: ONlit-french@hibbertco.com

English Phone: (+1) 303–308–7142 (M–F 12:00pm to 5:00pm UK Time)

Email: ONlit@hibbertco.com

EUROPEAN TOLL-FREE ACCESS*: 00-800-4422-3781

*Available from Germany, France, Italy, England, Ireland

CENTRAL/SOUTH AMERICA:

Spanish Phone: 303-308-7143 (Mon-Fri 8:00am to 5:00pm MST)

Email: ONlit-spanish@hibbertco.com

ASIA/PACIFIC: LDC for ON Semiconductor – Asia Support

Phone: 303-675-2121 (Tue-Fri 9:00am to 1:00pm, Hong Kong Time)

Toll Free from Hong Kong & Singapore:

001-800-4422-3781 Email: ONlit-asia@hibbertco.com

JAPAN: ON Semiconductor, Japan Customer Focus Center 4–32–1 Nishi–Gotanda, Shinagawa–ku, Tokyo, Japan 141–8549

Phone: 81–3–5740–2745 **Email**: r14525@onsemi.com

ON Semiconductor Website: http://onsemi.com

For additional information, please contact your local Sales Representative.